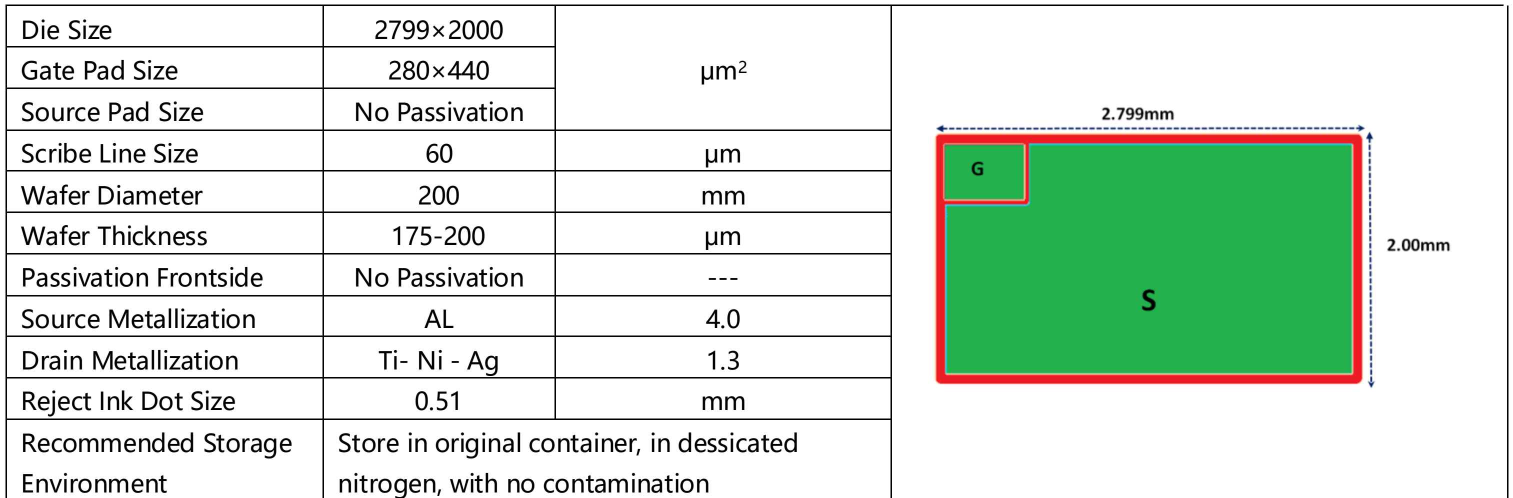
HSM

HMPD050R100

Mechanical Date

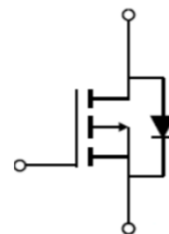


Die Size	2799×2000	µm²
Gate Pad Size	280×440	
Source Pad Size	No Passivation	
Scribe Line Size	60	µm
Wafer Diameter	200	mm
Wafer Thickness	175-200	µm
Passivation Frontside	No Passivation	---
Source Metallization	AL	4.0
Drain Metallization	Ti- Ni - Ag	1.3
Reject Ink Dot Size	0.51	mm
Recommended Storage Environment	Store in original container, in dessicated nitrogen, with no contamination	

Electrical Characteristics(TJ=25℃)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	-100			V	VGS=0V,ID=-250µA
$R_{DS(on)1}$	Static Drain-Source On-Resistance			50	mΩ	VGS=-10V,ID=-16A
$R_{DS(on)2}$	Static Drain-Source On-Resistance			55	mΩ	VGS=-4.5V,ID=-10A
$V_{GS(th)}$	Gate Threshold Voltage	-1.0		-3.0	V	VDS=VGS,ID=-250µA
I_{DSS}	Drain-to-Source Leakage Current			1	µA	VDS=-100V,VGS=0V,TJ=25℃
I_{GSS}	Gate-Body Leakage Current			±100	nA	VGS=±20V
V_{SD}	Body Diode Voltage			1.5	V	VGS=0V,ISD=-35A
T_J,T_{stg}	Operating and Storage Temperature Range	-55~+150			℃	

- -100V、-35A*，P-channel
- $R_{DS(on)}$=50mΩ(MAX)
- Ultra low Q_{gd}
- Fast switching



* Electrical characteristics are reported for the reference packaged part (TO-251/252/220) and can not be guaranteed in die

sales form.

Variations in customer packaging materials, dimensions and processes may affect parametric

performance.